MUR860D

Rev.F Jun.-2016

蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

Ultrafast Recovery Diode in a TO-252 Plastic Package.

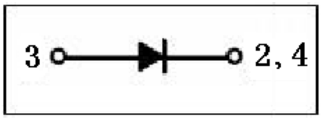
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

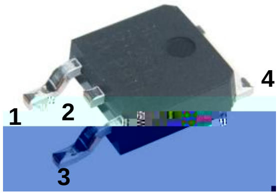
/ Applications

For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.

/ Equivalent Circuit



/ Pinning



PIN1 NC

PIN 2 Cathode

PIN 3 Anode

PIN 4:Case

/ h_{FE} Classifications & Marking

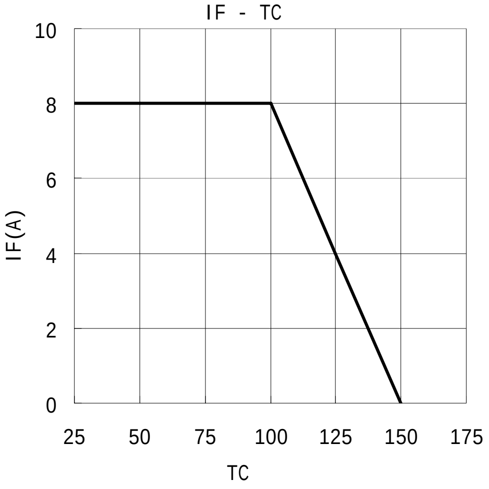
See Marking Instructions.

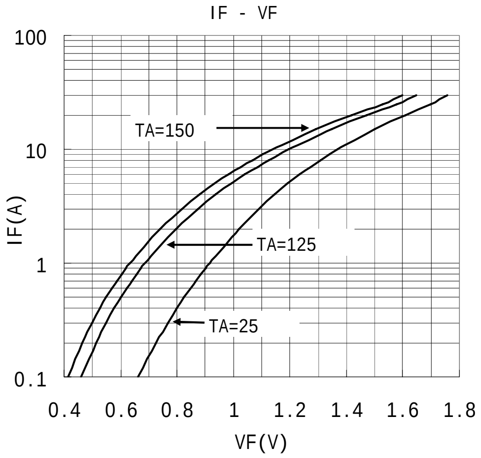
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
Working Peak Reverse Voltage	V_{RMS}	420	V
Average Rectified Forward Current	I_F	8	A
Non Repetitive Peak Surge Current	I_{FSM}	125	A
Thermal resistance, junction to case	$R_{\theta Jc}$	3.5	/W
Junction and Storage Temperature Range	T_j T_{stg}	-55 150	

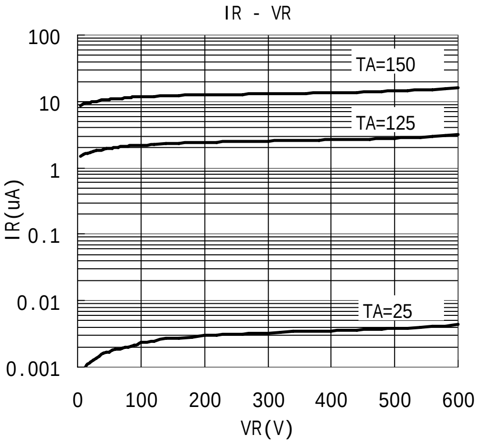
Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Reverse Voltage	V_{BR}	I_R=100uA		600			V
Forward Voltage	V_F	I_F=8A	Tc=25		1.4	1.7	V
		I_F=16A	Tc=25		1.7	2.1	V

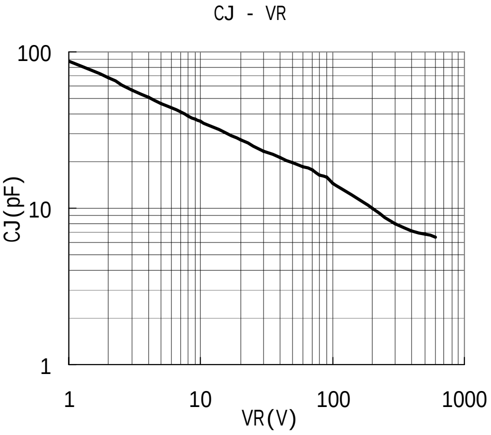
I_F

/ Electrical Characteristic Curve

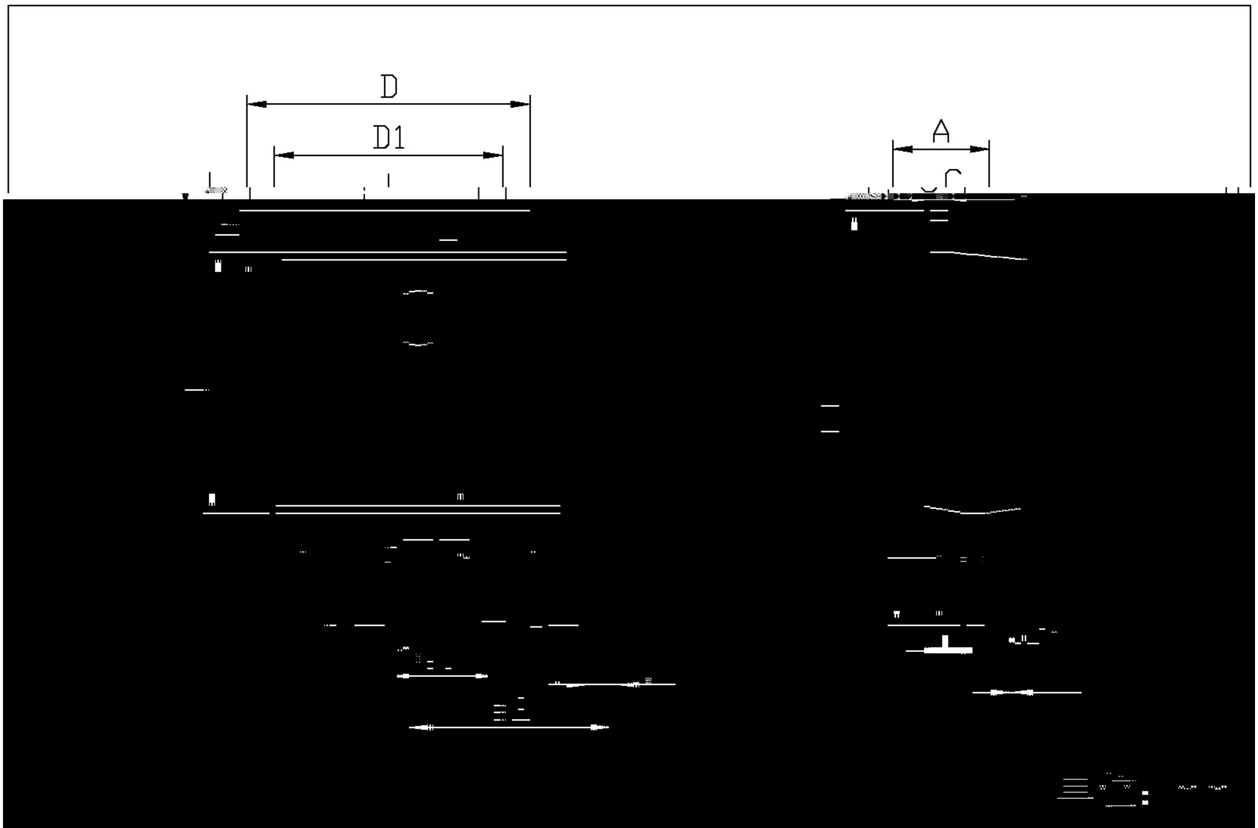








/ Package Dimensions



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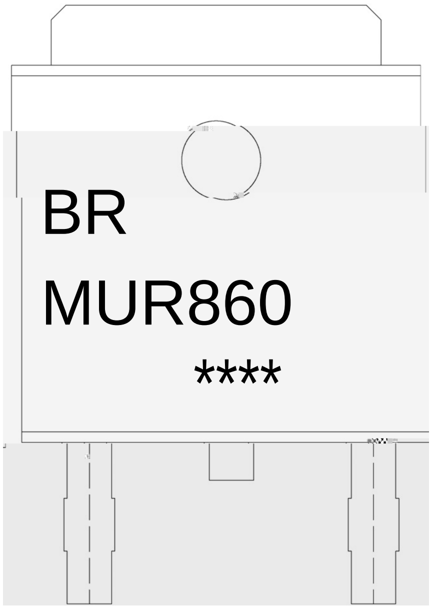
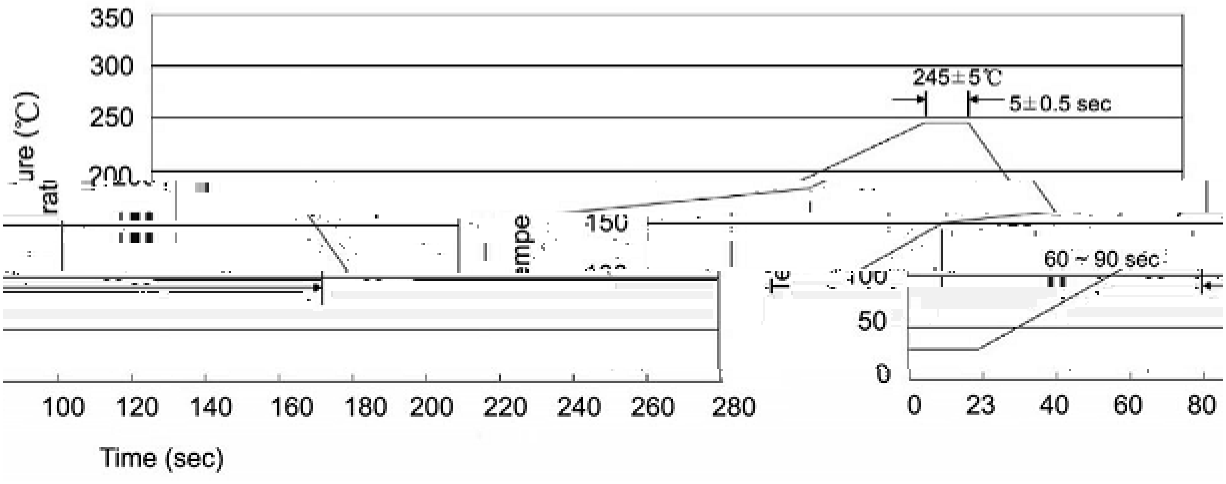
/ Marking Instructions



Note:

BR:	Company Code
	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



1 25 150 60 90sec;

2 245 5 5 0.5sec;

3 2 10 /sec.

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

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